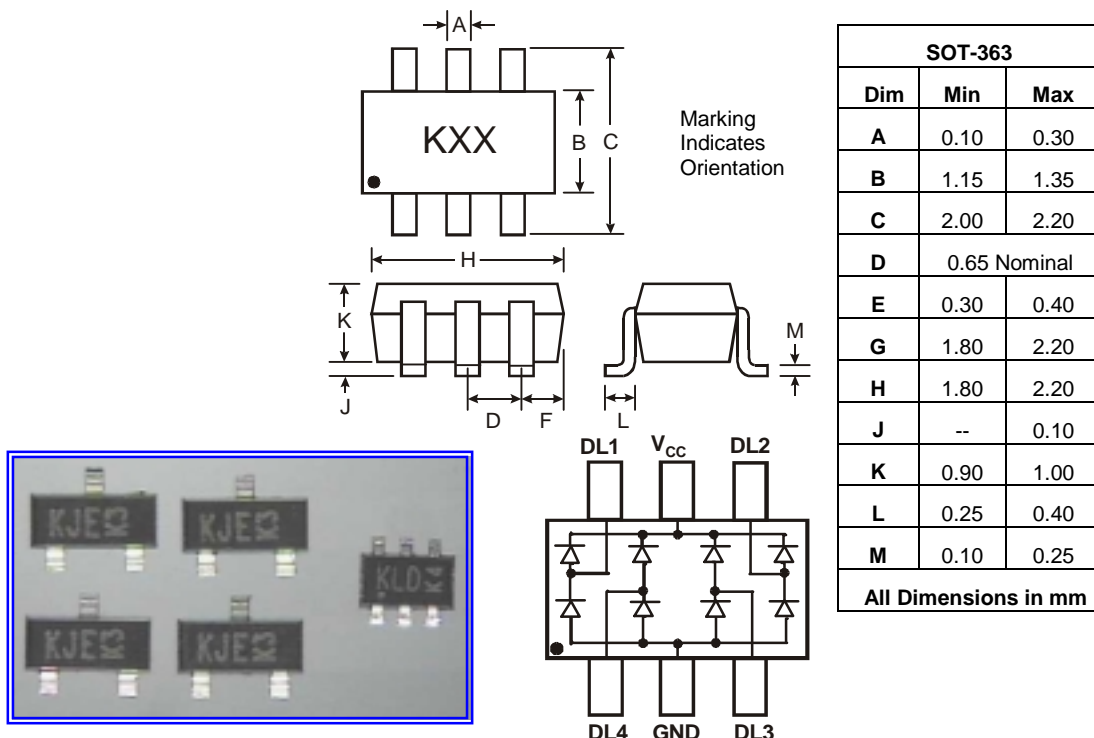


### Introducing Our New Compact 4-line Array Schottky Bus Terminator for High-Speed Data Systems: QSBT40 !



#### Key Features

- Diodes Inc's unique ASMCC (Application Specific Multi-Chip Component) high density implementation.
- Four data line terminators in one SOT-363 surface mount package.
- Rugged discrete Schottky die construction for high surge capability.
- Eight diodes arranged as four series-connected pairs.
- Low Schottky forward voltage, far superior to switching diode (BAV99) approaches.
- Low capacitance for high speed interfaces.
- Provides transient protection for high-speed data lines in accordance with: IEC 1000-4-2 (ESD), IEC 1000-4-4 (EFT), and IEC 1000-4-5 (Lightning)

#### Availability

- ☐ Samples Now In Stock
- ☐ Production Quantity Lead Time: Stock 6 weeks
- ☐ Data Sheet at: [www.diodes.com](http://www.diodes.com)

## Desirable Benefits

- Effectively terminates data lines avoiding complex impedance matching.
- Termination remains effective after changing data line configuration.
- Overshoots and transients clamped to Vcc and Ground.
- Up to 10:1 board space reduction over discrete Schottky diodes, with corresponding component placement cost savings.
- Compact 4-line array approach allows more effective and efficient distributed layout compared to multi-line monolithic arrays.

## Applications – End Equipment

- 1) Designed to protect the sensitive I/O ports of TTL and CMOS ICs from over voltages caused by induced electrical transients. Typical applications include:
  - Data line protection for RS-232, RS-422, and RS-485 transceivers.
  - Micro-controller input port protection.
  - Secondary protection for T1 Line Cards
  - LAN/WAN Equipment
  - Latch-Up protection
  - Video protection
  - Set Top Box I/O line protection
  - Ethernet 10-Base-T protection
  - Protection of memory devices
- 2) Designed to provide Bus Termination for High Speed Data Systems --  
This low capacitance device appears virtually transparent to the data signal, however, effectively dissipates an over/under voltage to the Vcc or Ground rail during a voltage transient or a pulse reflection.
- 3) A compact solution to providing the necessary high speed data line termination, ensuring:
  - increased noise immunity,
  - reduced cross-talk between lines, and
  - reduced propagation delays resulting in reduced improper operation and data loss to a devices input circuitry.

Typical applications include:

High speed parallel data communication such as:

Hard Disk Drives  
DAT Drives  
Disc Arrays  
Network Peripherals  
Termination of data lines  
Termination networks

## Ways It Surpasses Its Competition

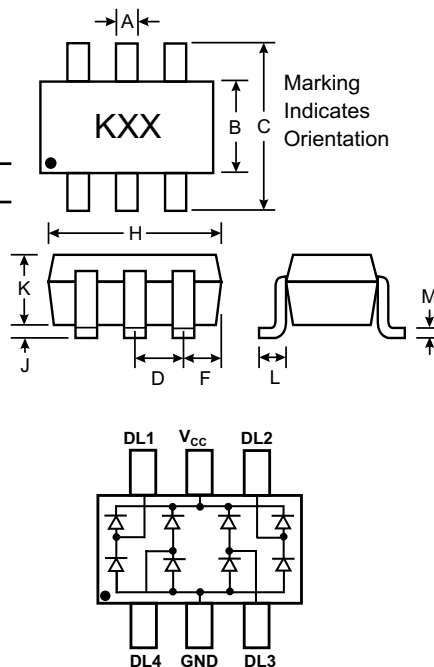
- Far more rugged than monolithic arrays
- Much lower cost than monolithic arrays
- Ease of layout
- Ease of placement
- Significant space advantage over other discrete Schottky approaches

### Features

- Low Forward Voltage Drop
- Fast Switching
- Very High Density
- Ultra-Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection

### Mechanical Data

- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See Diagrams Below
- Weight: 0.006 grams (approx.)
- Marking Code: KST



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	30	V
Forward Continuous Current	$I_{FM}$	200	mA
Non-Repetitive Peak Forward Surge Current @ $t < 1.0\text{s}$	$I_{FSM}$	600	mA
Power Dissipation	$P_d$	200	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	K/W
Operating and Storage Temperature Range	$T_j$ , $T_{STG}$	-55 to +125 -65 to +125	$^\circ\text{C}$

### Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Typ	Max	Unit	Test Condition
Maximum Forward Voltage	$V_{FM}$	—	280 350 450 550 1000	mV	$I_F = 0.1\text{mA}$ , $t_p < 300\mu\text{s}$ $I_F = 1.0\text{mA}$ , $t_p < 300\mu\text{s}$ $I_F = 10\text{mA}$ , $t_p < 300\mu\text{s}$ $I_F = 30\text{mA}$ , $t_p < 300\mu\text{s}$ $I_F = 100\text{mA}$ , $t_p < 300\mu\text{s}$
Maximum Peak Reverse Current	$I_{RM}$	—	2	$\mu\text{A}$	$V_R = 25\text{V}$
Junction Capacitance (Note 1)	$C_j$	10.0	—	pF	$V_R = 0$ , $f = 1.0\text{MHz}$
Reverse Recovery Time	$t_{rr}$	—	5.0	ns	$I_F = I_R = 10\text{mA}$ , $t_{rr} = 0.1 \times I_R$ , $R_L = 100\Omega$

Notes: 1. At  $V_R = 0\text{V}$ , DL(X) to  $V_{CC}$  or GND.